

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

HN2S01F

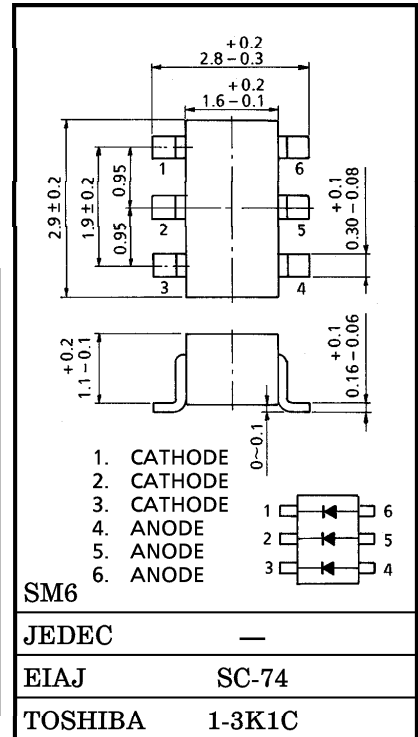
LOW VOLTAGE HIGH SPEED SWITCHING APPLICATION

Unit in mm

- HN2S01F is composed of 3 independent diodes.
- Low Forward Voltage : $V_F=0.23V$ (TYP.) @ $I_F=5mA$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200*	mA
Average Forward Current	I_O	100*	mA
Surge Current (10ms)	I_{FSM}	1*	A
Power Dissipation	P	300	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~125	$^\circ C$
Operating Temperature Range	T_{opr}	-40~100	$^\circ C$



* : This is the Maximum Ratings of single diode (Q1 or Q2 or Q3).
 In the case of using 2 or 3 diodes, the Maximum Ratings per diode is 75% of the single diode one.

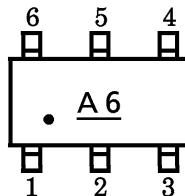
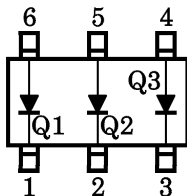
Weight : 0.015g

ELECTRICAL CHARACTERISTICS (Q1 Q2 Q3 COMMON, $T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F=1mA$	—	0.18	—	V
	$V_F(2)$	$I_F=5mA$	—	0.23	0.30	
	$V_F(3)$	$I_F=100mA$	—	0.35	0.50	
Reverse Current	I_R	$V_R=10V$	—	—	20	μA
Total Capacitance	C_T	$V_R=0, f=1MHz$	—	20	40	pF

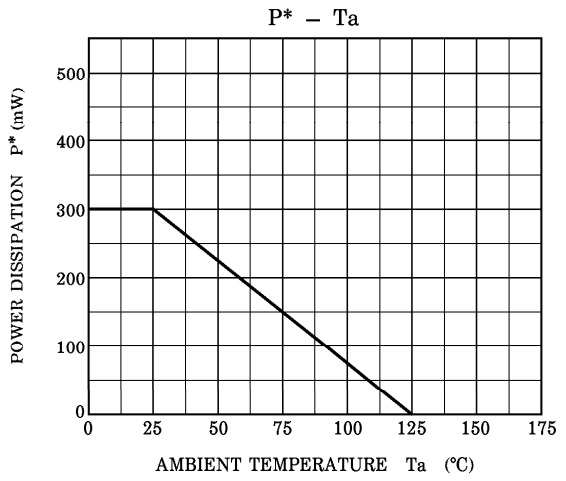
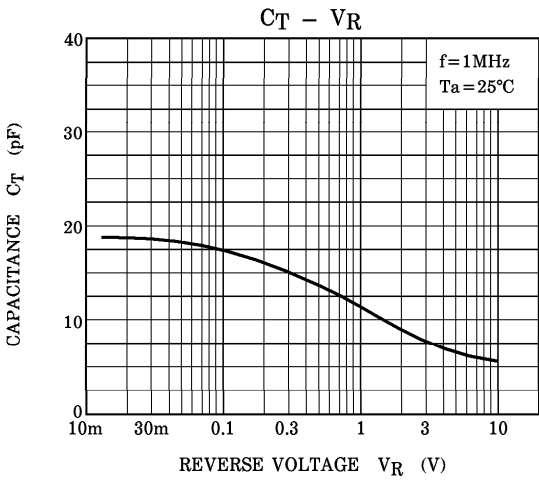
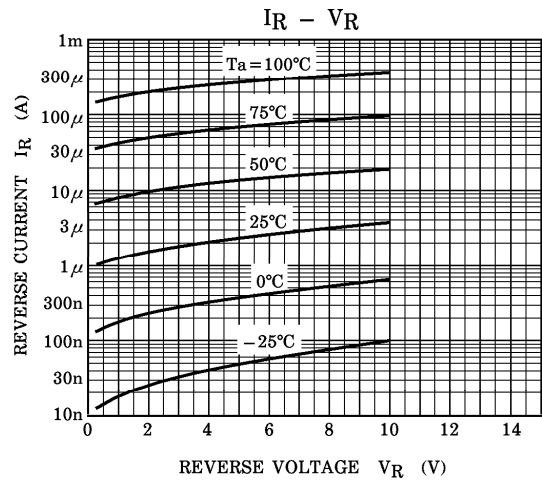
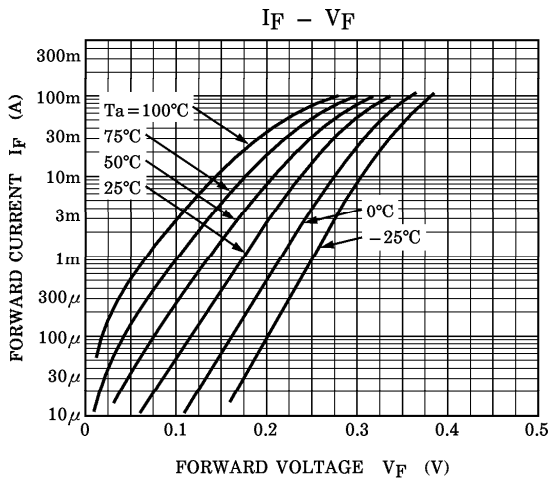
PIN ASSIGNMENT (TOP VIEW)

MARKING



961001EAA2

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* : Total Rating